Mauritius C M Van De Sanden

List of Publications by Year
in descending order

469 papers	19,894 citations	12330 69 h-index	18130 120 g-index
478 all docs	478 docs citations	478 times ranked	13295 citing authors

#	Article	IF	Citations
1	Observation and rationalization of nitrogen oxidation enabled only by coupled plasma and catalyst. Nature Communications, 2022, 13, 402.	12.8	23
2	The Chemical Origins of Plasma Contraction and Thermalization in CO₂ Microwave Discharges. Journal of Physical Chemistry Letters, 2022, 13, 1203-1208.	4.6	10
3	Charged particle kinetics and gas heating in CO₂ microwave plasma contraction: comparisons of simulations and experiments. Plasma Sources Science and Technology, 2022, 31, 055005.	3.1	11
4	The 2022 Plasma Roadmap: low temperature plasma science and technology. Journal Physics D: Applied Physics, 2022, 55, 373001.	2.8	139
5	Operando attenuated total reflection Fourier-transform infrared (ATR-FTIR) spectroscopy for water splitting. Journal Physics D: Applied Physics, 2021, 54, 133001.	2.8	12
6	Electrochemical Activation of Atomic Layer-Deposited Cobalt Phosphate Electrocatalysts for Water Oxidation. ACS Catalysis, 2021, 11, 2774-2785.	11.2	41
7	Operational Strategies to Improve the Performance and Longâ€Term Cyclability of Intermediate Temperature Sodiumâ€Sulfur Batteries. ChemElectroChem, 2021, 8, 1156-1166.	3.4	7
8	Revisiting spontaneous Raman scattering for direct oxygen atom quantification. Optics Letters, 2021, 46, 2172.	3.3	8
9	High-Throughput Computational Screening of Cubic Perovskites for Solid Oxide Fuel Cell Cathodes. Journal of Physical Chemistry Letters, 2021, 12, 4160-4165.	4.6	10
10	Resolving discharge parameters from atomic oxygen emission. Plasma Sources Science and Technology, 2021, 30, 065022.	3.1	8
11	Flame bands: CO + O chemiluminescence as a measure of gas temperature. Journal Physics D: Applied Physics, 2021, 54, 374005.	2.8	3
12	Redefining the Microwave Plasma-Mediated CO₂ Reduction Efficiency Limit: The Role of Oâ€“CO₂ Association. ACS Energy Letters, 2021, 6, 2876-2881.	17.4	19
13	Rational Design of Photoelectrodes for the Fully Integrated Polymer Electrode Membraneâ€“Photoelectrochemical Water-Splitting System: A Case Study of Bismuth Vanadate. ACS Applied Energy Materials, 2021, 4, 9600-9610.	5.1	10
14	Plasma Activated Electrochemical Ammonia Synthesis from Nitrogen and Water. ACS Energy Letters, 2021, 6, 313-319.	17.4	44
15	Plasma Driven Exsolution for Nanoscale Functionalization of Perovskite Oxides. Small Methods, 2021, 5, e2100868.	8.6	19
16	Mode resolved heating dynamics in pulsed microwave CO2 plasma from laser Raman scattering. Journal Physics D: Applied Physics, 2020, 53, 054002.	2.8	19
17	Symmetrical Exsolution of Rh Nanoparticles in Solid Oxide Cells for Efficient Syngas Production from Greenhouse Gases. ACS Catalysis, 2020, 10, 1278-1288.	11.2	52
18	Implications of thermo-chemical instability on the contracted modes in CO₂ microwave plasmas. Plasma Sources Science and Technology, 2020, 29, 025005.	3.1	45

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19	Charge carrier dynamics and photocatalytic activity of {111} and {100} faceted Ag3PO4 particles. Journal of Chemical Physics, 2020, 152, 244710.	3.0	6
20	CO₂ Conversion in Nonuniform Discharges: Disentangling Dissociation and Recombination Mechanisms. Journal of Physical Chemistry C, 2020, 124, 16806-16819.	3.1	36
21	Enhancing the Electrocatalytic Activity of Redox Stable Perovskite Fuel Electrodes in Solid Oxide Cells by Atomic Layer-Deposited Pt Nanoparticles. ACS Sustainable Chemistry and Engineering, 2020, 8, 12646-12654.	6.7	13
22	Emission spectroscopy of He lines in high-density plasmas in Magnum-PSI. AIP Advances, 2020, 10, .	1.3	12
23	Insight into contraction dynamics of microwave plasmas for CO₂ conversion from plasma chemistry modelling. Plasma Sources Science and Technology, 2020, 29, 105014.	3.1	27
24	Plasma activation of N₂, CH₄and CO₂: an assessment of the vibrational non-equilibrium time window. Plasma Sources Science and Technology, 2020, 29, 115001.	3.1	22
25	Excitation and relaxation of the asymmetric stretch mode of CO₂ in a pulsed glow discharge. Plasma Sources Science and Technology, 2019, 28, 035011.	3.1	27
26	Plasma-Activated Electrolysis for Cogeneration of Nitric Oxide and Hydrogen from Water and Nitrogen. ACS Energy Letters, 2019, 4, 2091-2095.	17.4	35
27	Co-electrolysis of H2O and CO2 on exsolved Ni nanoparticles for efficient syngas generation at controllable H2/CO ratios. Applied Catalysis B: Environmental, 2019, 258, 117950.	20.2	53
28	Role of Electronâ€“Ion Dissociative Recombination in $$hbox {CH}_{4}$$ Microwave Plasma on Basis of Simulations and Measurements of Electron Energy. Plasma Chemistry and Plasma Processing, 2019, 39, 1275-1289.	2.4	4
29	Solar Hydrogen Generation from Ambient Humidity Using Functionalized Porous Photoanodes. ACS Applied Materials & Interfaces, 2019, 11, 41267-41280.	8.0	17
30	Characterization of CO₂ microwave plasma based on the phenomenon of skin-depth-limited contraction. Plasma Sources Science and Technology, 2019, 28, 115022.	3.1	30
31	In Situ Observation of Nanoparticle Exsolution from Perovskite Oxides: From Atomic Scale Mechanistic Insight to Nanostructure Tailoring. ACS Nano, 2019, 13, 12996-13005.	14.6	144
32	Validation of the Fokkerâ€“Planck Approach to Vibrational Kinetics in CO₂ Plasma. Journal of Physical Chemistry C, 2019, 123, 22823-22831.	3.1	22
33	Atmospheric-pressure silica-like thin film deposition using 200â€‰kHz/13.56 MHz dual frequency excitation. Journal Physics D: Applied Physics, 2019, 52, 355201.	2.8	6
34	Electrochemistry of Sputtered Hematite Photoanodes: A Comparison of Metallic DC versus Reactive RF Sputtering. ACS Omega, 2019, 4, 9262-9270.	3.5	7
35	Numerical model for the determination of the reduced electric field in a CO₂ microwave plasma derived by the principle of impedance matching. Plasma Sources Science and Technology, 2019, 28, 075016.	3.1	22
36	High and intermediate temperature sodiumâ€“sulfur batteries for energy storage: development, challenges and perspectives. RSC Advances, 2019, 9, 5649-5673.	3.6	68

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37	Fokkerâ€“Planck equation for chemical reactions in plasmas. Rendiconti Lincei, 2019, 30, 25-30.	2.2	3
38	28. Plasma-based CO₂ conversion. , 2019, , 585-634.		5
39	The importance of thermal dissociation in CO₂ microwave discharges investigated by power pulsing and rotational Raman scattering. Plasma Sources Science and Technology, 2019, 28, 055015.	3.1	55
40	An Electrochemical Study on the Cathode of the Intermediate Temperature Tubular Sodium-Sulfur (NaS) Battery. Journal of the Electrochemical Society, 2019, 166, A135-A142.	2.9	23
41	Atomic layer deposition of cobalt phosphate thin films for the oxygen evolution reaction. Electrochemistry Communications, 2019, 98, 73-77.	4.7	19
42	The role of carrier gas flow in roll-to-roll AP-PECVD synthesized silica moisture barrier films. Surface and Coatings Technology, 2018, 339, 20-26.	4.8	8
43	Preferential vibrational excitation in microwave nitrogen plasma assessed by Raman scattering. Plasma Sources Science and Technology, 2018, 27, 055006.	3.1	18
44	Atmospheric-pressure diffuse dielectric barrier discharges in Ar/O₂gas mixture using 200â€‰kHz/13.56 MHz dual frequency excitation. Journal Physics D: Applied Physics, 2018, 51, 114002.	2.8	20
45	Improving uniformity of atmospheric-pressure dielectric barrier discharges using dual frequency excitation. Plasma Sources Science and Technology, 2018, 27, 01LT01.	3.1	9
46	A rotational Raman study under non-thermal conditions in a pulsed CO₂glow discharge. Plasma Sources Science and Technology, 2018, 27, 045009.	3.1	25
47	Plasma for electrification of chemical industry: a case study on CO₂reduction. Plasma Physics and Controlled Fusion, 2018, 60, 014019.	2.1	71
48	Plasma conductivity as a probe for ambient air admixture in an atmospheric pressure plasma jet. Plasma Chemistry and Plasma Processing, 2018, 38, 63-74.	2.4	1
49	The role of the gradient film properties in silica moisture barriers synthesized in a rollâ€toâ€roll atmospheric pressure plasma enhanced CVD reactor. Plasma Processes and Polymers, 2018, 15, 1700093.	3.0	12
50	Visible detection of performance controlling pinholes in silica encapsulation films. Journal Physics D: Applied Physics, 2018, 51, 43LT01.	2.8	1
51	Numerical simulation of atmospheric-pressure 200 kHz/13.56 MHz dual-frequency dielectric barrier discharges. Plasma Sources Science and Technology, 2018, 27, 105016.	3.1	12
52	Nonâ€oxidative methane coupling to C₂ hydrocarbons in a microwave plasma reactor. Plasma Processes and Polymers, 2018, 15, 1800087.	3.0	25
53	Vibrational Kinetics in Plasma as a Functional Problem: A Flux-Matching Approach. Journal of Physical Chemistry A, 2018, 122, 7918-7923.	2.5	20
54	Mechanisms of elementary hydrogen ion-surface interactions during multilayer graphene etching at high surface temperature as a function of flux. Carbon, 2018, 137, 527-532.	10.3	10

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55	Zeolites for CO₂â€“COâ€“O₂ Separation to Obtain CO₂-Neutral Fuels. ACS Applied Materials & Interfaces, 2018, 10, 20512-20520.	8.0	30
56	Variable roughness development in statically deposited SiO₂ thin films: a spatially resolved surface morphology analysis. Journal Physics D: Applied Physics, 2018, 51, 285303.	2.8	4
57	Plasma radiation studies in Magnum-PSI using resistive bolometry. Nuclear Fusion, 2018, 58, 106006.	3.5	12
58	How the alternating degeneracy in rotational Raman spectra of CO2and C2H2reveals the vibrational temperature. Applied Optics, 2018, 57, 5694.	1.8	10
59	Nanostructuring of iron thin films by high flux low energy helium plasma. Thin Solid Films, 2017, 631, 50-56.	1.8	11
60	Defect prevention in silica thin films synthesized using AP-PECVD for flexible electronic encapsulation. Journal Physics D: Applied Physics, 2017, 50, 25LT01.	2.8	7
61	Atomic layer deposition of highly dispersed Pt nanoparticles on a high surface area electrode backbone for electrochemical promotion of catalysis. Electrochemistry Communications, 2017, 84, 40-44.	4.7	17
62	Time evolution of vibrational temperatures in a CO₂glow discharge measured with infrared absorption spectroscopy. Plasma Sources Science and Technology, 2017, 26, 115008.	3.1	73
63	Atomistic simulations of graphite etching at realistic time scales. Chemical Science, 2017, 8, 7160-7168.	7.4	6
64	Fast nanostructured carbon microparticle synthesis by one-step high-flux plasma processing. Carbon, 2017, 124, 403-414.	10.3	5
65	Atomic hydrogen induced defect kinetics in amorphous silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, 05C307.	2.1	5
66	The 2017 Plasma Roadmap: Low temperature plasma science and technology. Journal Physics D: Applied Physics, 2017, 50, 323001.	2.8	710
67	Infrared gas phase study on plasma-polymer interactions in high-current diffuse dielectric barrier discharge. Journal of Applied Physics, 2017, 121, 243301.	2.5	5
68	Oscillatory vapour shielding of liquid metal walls in nuclear fusion devices. Nature Communications, 2017, 8, 192.	12.8	43
69	Insight into CO₂ Dissociation in Plasma from Numerical Solution of a Vibrational Diffusion Equation. Journal of Physical Chemistry C, 2017, 121, 19568-19576.	3.1	35
70	Control of the intrinsic microstructure in AP-PECVD synthesised amorphous silica thin films. RSC Advances, 2017, 7, 52274-52282.	3.6	3
71	An analytical force balance model for dust particles with size up to several Debye lengths. Physics of Plasmas, 2017, 24, 113702.	1.9	3
72	On the synergistic effect of inorganic/inorganic barrier layers: An ellipsometric porosimetry investigation. Plasma Processes and Polymers, 2017, 14, 1700012.	3.0	2

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73	Homogeneous CO₂ conversion by microwave plasma: Wave propagation and diagnostics. Plasma Processes and Polymers, 2017, 14, 1600120.	3.0	90
74	Atmospheric pressure rollâ€toâ€roll plasma enhanced CVD of high quality silicaâ€like bilayer encapsulation films. Plasma Processes and Polymers, 2017, 14, 1600143.	3.0	21
75	Plasmaâ€driven dissociation of CO₂ for fuel synthesis. Plasma Processes and Polymers, 2017, 14, 1600126.	3.0	152
76	The electrochemistry of iron oxide thin films nanostructured by high ion flux plasma exposure. Electrochimica Acta, 2017, 258, 709-717.	5.2	15
77	Non-equilibrium Microwave Plasma for Efficient High Temperature Chemistry. Journal of Visualized Experiments, 2017, , .	0.3	4
78	Analysis of temporal evolution of quantum dot surface chemistry by surface-enhanced Raman scattering. Scientific Reports, 2016, 6, 29508.	3.3	11
79	Fluid modelling of CO2 dissociation in a dielectric barrier discharge. Journal of Applied Physics, 2016, 119, .	2.5	77
80	Dielectric barrier discharges revisited: the case for mobile surface charge. Plasma Sources Science and Technology, 2016, 25, 03LT03.	3.1	17
81	In situspectroscopic ellipsometry during atomic layer deposition of Pt, Ru and Pd. Journal Physics D: Applied Physics, 2016, 49, 115504.	2.8	27
82	Oxygen Evolution at Hematite Surfaces: The Impact of Structure and Oxygen Vacancies on Lowering the Overpotential. Journal of Physical Chemistry C, 2016, 120, 18201-18208.	3.1	107
83	Back Cover: Plasma Process. Polym. 1â•2016. Plasma Processes and Polymers, 2016, 13, 202-202.	3.0	1
84	Expanding Thermal Plasma Deposition of Alâ€Doped ZnO: On the Effect of the Plasma Chemistry on Film Growth Mechanisms. Plasma Processes and Polymers, 2016, 13, 54-69.	3.0	5
85	Self-Regulated Plasma Heat Flux Mitigation Due to Liquid Sn Vapor Shielding. Physical Review Letters, 2016, 116, 135002.	7.8	59
86	Molecular dynamics simulations of ballistic He penetration into W fuzz. Nuclear Fusion, 2016, 56, 126015.	3.5	22
87	CO2-Neutral Fuels. Europhysics News, 2016, 47, 22-26.	0.3	22
88	Gasâ€Phase Plasma Synthesis of Freeâ€Standing Silicon Nanoparticles for Future Energy Applications. Plasma Processes and Polymers, 2016, 13, 19-53.	3.0	16
89	Special Issue of Papers by Plenary and Topical Invited Lecturers at the 22nd International Symposium on Plasma Chemistry (ISPC 22), 5â€“10 July 2015, Antwerp, Belgium: Introduction. Plasma Chemistry and Plasma Processing, 2016, 36, 1-2.	2.4	13
90	Synergy Between Plasmaâ€Assisted ALD and Rollâ€toâ€Roll Atmospheric Pressure PEâ€CVD Processing of Moisture Barrier Films on Polymers. Plasma Processes and Polymers, 2016, 13, 311-315.	3.0	18

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91	Surface Modifications Induced by High Fluxes of Low Energy Helium Ions. Scientific Reports, 2015, 5, 9779.	3.3	39
92	Characterization of Nanocrystal Size Distribution using Raman Spectroscopy with a Multi-particle Phonon Confinement Model. Journal of Visualized Experiments, 2015, , e53026.	0.3	4
93	Towards Rollâ€toâ€Roll Deposition of High Quality Moisture Barrier Films on Polymers by Atmospheric Pressure Plasma Assisted Process. Plasma Processes and Polymers, 2015, 12, 545-554.	3.0	53
94	Relation between light trapping and surface topography of plasma textured crystalline silicon wafers. Progress in Photovoltaics: Research and Applications, 2015, 23, 352-366.	8.1	9
95	The influence of partial surface discharging on the electrical characterization of DBDs. Plasma Sources Science and Technology, 2015, 24, 015016.	3.1	70
96	Improved size distribution control of silicon nanocrystals in a spatially confined remote plasma. Plasma Sources Science and Technology, 2015, 24, 015030.	3.1	3
97	The impact of the nano-pore filling on the performance of organosilicon-based moisture barriers. Thin Solid Films, 2015, 595, 251-257.	1.8	13
98	The relation between the production efficiency of nitrogen atoms and the electrical characteristics of a dielectric barrier discharge. Plasma Sources Science and Technology, 2015, 24, 045006.	3.1	21
99	Note: Rotational Raman scattering on CO2 plasma using a volume Bragg grating as a notch filter. Review of Scientific Instruments, 2015, 86, 046106.	1.3	24
100	Gas temperature in transient CO2plasma measured by Raman scattering. Journal Physics D: Applied Physics, 2015, 48, 155201.	2.8	18
101	Residual gas entering high density hydrogen plasma: rarefaction due to rapid heating. Plasma Sources Science and Technology, 2015, 24, 025020.	3.1	4
102	Taming microwave plasma to beat thermodynamics in CO₂ dissociation. Faraday Discussions, 2015, 183, 233-248.	3.2	150
103	Waveguide Nanowire Superconducting Single-Photon Detectors Fabricated on GaAs and the Study of Their Optical Properties. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 1-10.	2.9	188
104	CO and byproduct formation during CO2 reduction in dielectric barrier discharges. Journal of Applied Physics, 2014, 116, .	2.5	95
105	Nucleation of silicon nanocrystals in a remote plasma without subsequent coagulation. Journal of Applied Physics, 2014, 115, 244301.	2.5	10
106	On the intrinsic moisture permeation rate of remote microwave plasma-deposited silicon nitride layers. Thin Solid Films, 2014, 558, 54-61.	1.8	22
107	High throughput deposition of hydrogenated amorphous carbon coatings on rubber with expanding thermal plasma. Surface and Coatings Technology, 2014, 245, 74-83.	4.8	9
108	Spontaneous synthesis of carbon nanowalls, nanotubes and nanotips using high flux density plasmas. Carbon, 2014, 68, 695-707.	10.3	20

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109	An improved thin film approximation to accurately determine the optical conductivity of graphene from infrared transmittance. Applied Physics Letters, 2014, 105, 013105.	3.3	8
110	Nanostructuring of Iron Surfaces by Low-Energy Helium Ions. ACS Applied Materials & Interfaces, 2014, 6, 3462-3468.	8.0	40
111	On the role of nanoporosity in controlling the performance of moisture permeation barrier layers. Microporous and Mesoporous Materials, 2014, 188, 163-171.	4.4	35
112	VEIT 2014. Journal of Physics: Conference Series, 2014, 514, 011001.	0.4	0
113	Direct ion flux measurements at high-pressure-depletion conditions for microcrystalline silicon deposition. Journal of Applied Physics, 2013, 114, 063305.	2.5	19
114	Efficient Plasma Route to Nanostructure Materials: Case Study on the Use of m-WO₃ for Solar Water Splitting. ACS Applied Materials & Interfaces, 2013, 5, 7621-7625.	8.0	96
115	Direct characterization of nanocrystal size distribution using Raman spectroscopy. Journal of Applied Physics, 2013, 114, 134310.	2.5	57
116	PPPS-2013: CO<inf>2</inf> conversion in non-thermal plasma processes. , 2013, , .		0
117	Morphological Description of Ultraâ€Smooth Organoâ€Silicone Layers Synthesized Using Atmospheric Pressure Dielectric Barrier Discharge Assisted PECVD. Plasma Processes and Polymers, 2013, 10, 313-319.	3.0	13
118	Ultrahigh throughput plasma processing of free standing silicon nanocrystals with lognormal size distribution. Journal of Applied Physics, 2013, 113, .	2.5	36
119	PPPS-2013: Infrared gas phase studies and scaling parameters in PE-CVD processes at atmospheric pressure using high-current dielectric barrier discharges. , 2013, , .		0
120	Carbon monoxide-induced reduction and healing of graphene oxide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	17
121	Chemical sputtering of graphite by low temperature nitrogen plasmas at various substrate temperatures and ion flux densities. Journal of Applied Physics, 2013, 114, .	2.5	10
122	On the effect of the underlying ZnO:Al layer on the crystallization kinetics of hydrogenated amorphous silicon. Applied Physics Letters, 2013, 102, .	3.3	2
123	Substrate-biasing during plasma-assisted atomic layer deposition to tailor metal-oxide thin film growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	95
124	Ion-induced effects on grain boundaries and <i>a</i>-Si:H tissue quality in microcrystalline silicon films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	5
125	Initiated-chemical vapor deposition of organosilicon layers: Monomer adsorption, bulk growth, and process window definition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	32
126	Solid-phase crystallization of ultra high growth rate amorphous silicon films. Journal of Applied Physics, 2012, 111, 103510.	2.5	8

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127	Influence of annealing and Al2O3 properties on the hydrogen-induced passivation of the Si/SiO2 interface. Journal of Applied Physics, 2012, 111, .	2.5	133
128	17th International Summer School on Vacuum, Electron, and Ion Technologies (VEIT 2011). Journal of Physics: Conference Series, 2012, 356, 011001.	0.4	1
129	The Relation Between the Bandgap and the Anisotropic Nature of Hydrogenated Amorphous Silicon. IEEE Journal of Photovoltaics, 2012, 2, 94-98.	2.5	28
130	Reaction mechanisms of atomic layer deposition of TaNx from Ta(NMe2)5 precursor and H2-based plasmas. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, 01A101.	2.1	22
131	Gas-Phase Hydrosilylation of Plasma-Synthesized Silicon Nanocrystals with Short- and Long-Chain Alkynes. Langmuir, 2012, 28, 17295-17301.	3.5	20
132	Improved conductivity of aluminum-doped ZnO: The effect of hydrogen diffusion from a hydrogenated amorphous silicon capping layer. Journal of Applied Physics, 2012, 111, 063715.	2.5	9
133	Controlling the resistivity gradient in aluminum-doped zinc oxide grown by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2012, 112, .	2.5	9
134	Remote plasma deposition of microcrystalline silicon thin-films: Film structure and the role of atomic hydrogen. Journal of Non-Crystalline Solids, 2012, 358, 379-386.	3.1	10
135	Synergistic etch rates during low-energetic plasma etching of hydrogenated amorphous carbon. Journal of Applied Physics, 2012, 112, .	2.5	18
136	Real time in situ spectroscopic ellipsometry of the growth and plasmonic properties of au nanoparticles on SiO2. Nano Research, 2012, 5, 513-520.	10.4	37
137	Atomic layer deposition for nanostructured Li-ion batteries. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	111
138	Detailed H(n= 2) density measurements in a magnetized hydrogen plasma jet. Plasma Sources Science and Technology, 2012, 21, 024009.	3.1	6
139	Surface passivation of phosphorusâ€diffused n⁺â€type emitters by plasmaâ€assisted atomicâ€layer deposited Al₂O₃. Physica Status Solidi - Rapid Research Letters, 2012, 6, 4-6.	2.4	73
140	Hydrogenated amorphous silicon pâ€“iâ€“n solar cells deposited under well controlled ion bombardment using pulseâ€shaped substrate biasing. Progress in Photovoltaics: Research and Applications, 2012, 20, 333-342.	8.1	5
141	Plasmaâ€enhanced Chemical Vapor Deposition of Aluminum Oxide Using Ultrashort Precursor Injection Pulses. Plasma Processes and Polymers, 2012, 9, 761-771.	3.0	19
142	Surface Dynamics of SiO₂â€like Films on Polymers Grown by DBD Assisted CVD at Atmospheric Pressure. Plasma Processes and Polymers, 2012, 9, 1194-1207.	3.0	15
143	In situ crystallization kinetics studies of plasma-deposited, hydrogenated amorphous silicon layers. Journal of Applied Physics, 2012, 111, 033508.	2.5	9
144	Evidence of the filling of nano-porosity in SiO2-like layers by an initiated-CVD monomer. Microporous and Mesoporous Materials, 2012, 151, 434-439.	4.4	31

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145	Kinetic study of solid phase crystallisation of expanding thermal plasma deposited a-Si:H. Thin Solid Films, 2012, 520, 5820-5825.	1.8	5
146	Plasma-Assisted Atomic Layer Deposition: Basics, Opportunities, and Challenges. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	678
147	Surface Hydride Composition of Plasma-Synthesized Si Nanoparticles. Journal of Physical Chemistry C, 2011, 115, 20375-20379.	3.1	40
148	Ion and Photon Surface Interaction during Remote Plasma ALD of Metal Oxides. Journal of the Electrochemical Society, 2011, 158, G88.	2.9	73
149	Microfocus infrared ellipsometry characterization of air-exposed graphene flakes. Applied Physics Letters, 2011, 99, 061909.	3.3	15
150	Substrate Biasing during Plasma-Assisted ALD for Crystalline Phase-Control of TiO2 Thin Films. Electrochemical and Solid-State Letters, 2011, 15, G1-G3.	2.2	46
151	Er3+ and Si luminescence of atomic layer deposited Er-doped Al2O3 thin films on Si(100). Journal of Applied Physics, 2011, 109, .	2.5	25
152	On the oxidation mechanism of microcrystalline silicon thin films studied by Fourier transform infrared spectroscopy. Journal of Non-Crystalline Solids, 2011, 357, 884-887.	3.1	30
153	Improved adhesion and tribological properties of fast-deposited hard graphite-like hydrogenated amorphous carbon films. Diamond and Related Materials, 2011, 20, 1266-1272.	3.9	16
154	Excellent Si surface passivation by low temperature SiO₂ using an ultrathin Al₂O₃ capping film. Physica Status Solidi - Rapid Research Letters, 2011, 5, 22-24.	2.4	77
155	Plasma-Assisted Deposition of Au/SiO2 Multi-layers as Surface Plasmon Resonance-Based Red-Colored Coatings. Plasmonics, 2011, 6, 255-260.	3.4	14
156	H₂: The Critical Juncture between Polymerization and Dissociation of Hydrocarbons in a Lowâ€temperature Plasma. Plasma Processes and Polymers, 2011, 8, 832-841.	3.0	3
157	On the Effect of the Amorphous Silicon Microstructure on the Grain Size of Solid Phase Crystallized Polycrystalline Silicon. Advanced Energy Materials, 2011, 1, 401-406.	19.5	21
158	Investigating the flow dynamics and chemistry of an expanding thermal plasma through CH(Aâ€“X) emission spectra. Journal Physics D: Applied Physics, 2011, 44, 355205.	2.8	0
159	On the role of atomic hydrogen during microcrystalline silicon thin-film deposition. , 2011, , .		0
160	Effect of ion bombardment on the a-Si:H based surface passivation of c-Si surfaces. Applied Physics Letters, 2011, 98, .	3.3	38
161	Population inversion in a magnetized hydrogen plasma expansion as a consequence of the molecular mutual neutralization process. Physical Review E, 2011, 83, 036412.	2.1	9
162	Atomic layer deposition of Ru from CpRu(CO)2Et using O2 gas and O2 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	51

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163	Controlling the fixed charge and passivation properties of Si(100)/Al2O3 interfaces using ultrathin SiO2 interlayers synthesized by atomic layer deposition. Journal of Applied Physics, 2011, 110, .	2.5	150
164	Influence of the Oxidant on the Chemical and Field-Effect Passivation of Si by ALD Al[sub 2]O[sub 3]. Electrochemical and Solid-State Letters, 2011, 14, H1.	2.2	151
165	In-situ X-ray diffraction analysis of the crystallisation of a-SI:H films deposited by the expanding thermal plasma technique. , 2011, , .		0
166	Dielectric Properties of Thermal and Plasma-Assisted Atomic Layer Deposited Al[sub 2]O[sub 3] Thin Films. Journal of the Electrochemical Society, 2011, 158, G21.	2.9	65
167	Remote Plasma ALD of SrTiO[sub 3] Using Cyclopentadienlyl-Based Ti and Sr Precursors. Journal of the Electrochemical Society, 2011, 158, G34.	2.9	28
168	Effective passivation of Si surfaces by plasma deposited SiOx/a-SiNx:H stacks. Applied Physics Letters, 2011, 98, .	3.3	67
169	Silicon surface passivation by ultrathin Al₂O₃ films synthesized by thermal and plasma atomic layer deposition. Physica Status Solidi - Rapid Research Letters, 2010, 4, 10-12.	2.4	185
170	Role of aâ€Si:H bulk in surface passivation of câ€Si wafers. Physica Status Solidi - Rapid Research Letters, 2010, 4, 172-174.	2.4	12
171	Hydrogenated amorphous silicon based surface passivation of câ€Si at high deposition temperature and rate. Physica Status Solidi - Rapid Research Letters, 2010, 4, 206-208.	2.4	10
172	Optical Characterization of Plasmaâ€Deposited SiO₂â€Like Layers on Anisotropic Polymeric Substrates. Plasma Processes and Polymers, 2010, 7, 766-774.	3.0	13
173	Smooth and Selfâ€Similar SiO₂â€like Films on Polymers Synthesized in Rollâ€toâ€Roll Atmospheric Pressureâ€PECVD for Gas Diffusion Barrier Applications. Plasma Processes and Polymers, 2010, 7, 635-639.	3.0	51
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